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(57) **ABSTRACT**

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An organic light emitting diode includes: a substrate; an encapsulation substrate facing the substrate and including a transmission region through which light is transmitted and an absorption region through which the light is not transmitted; a sealant between the substrate and the encapsulation substrate; and a pixel unit between the substrate and the encapsulation substrate, and including a plurality of pixels respectively including an organic light emitting element. The absorption region of the encapsulation substrate includes photoreactive crystals.

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CPC **H01L 27/3232** (2013.01); **H01L 51/56**
(2013.01); **H01L 27/323** (2013.01)

(58) **Field of Classification Search**
CPC H01L 27/3232; H01L 27/323; H01L 51/56
See application file for complete search history.

14 Claims, 5 Drawing Sheets

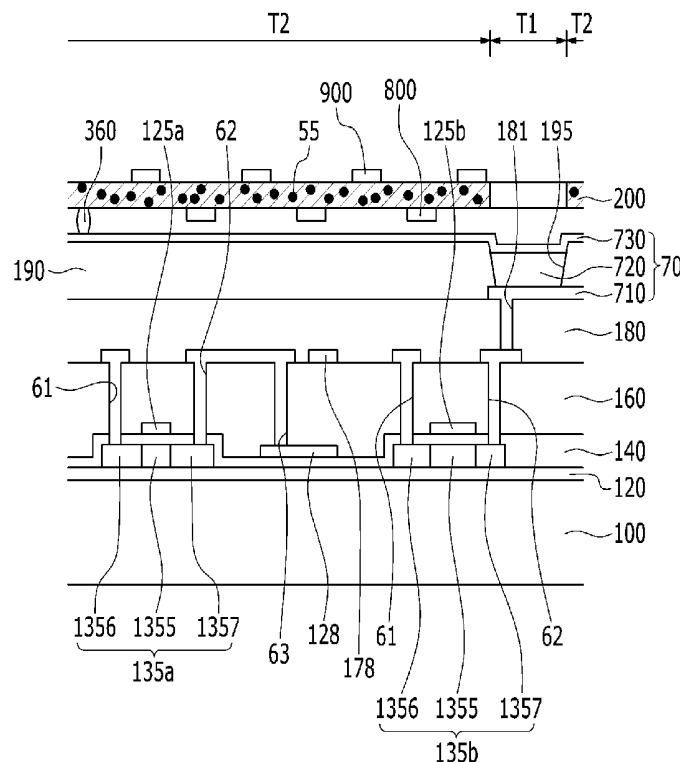


FIG. 1

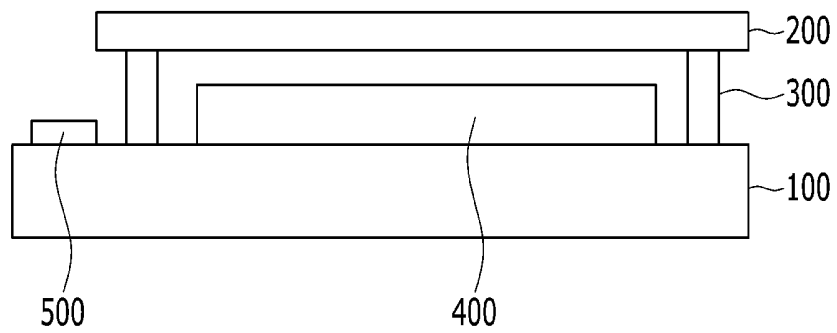


FIG. 2

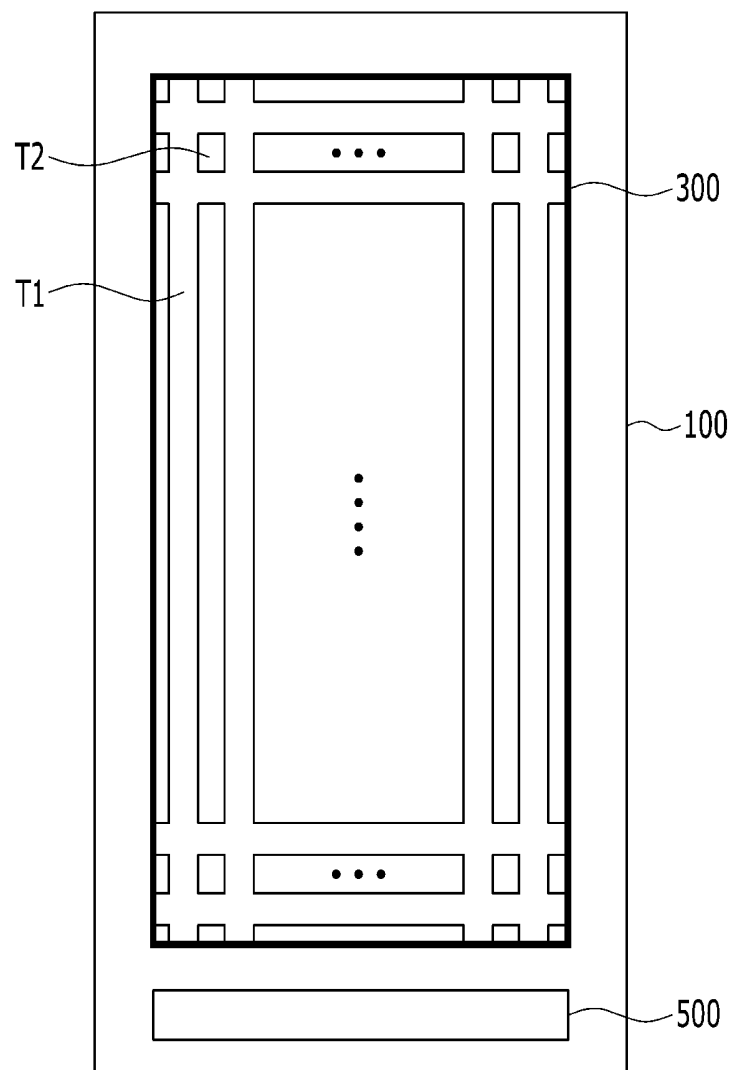


FIG. 3

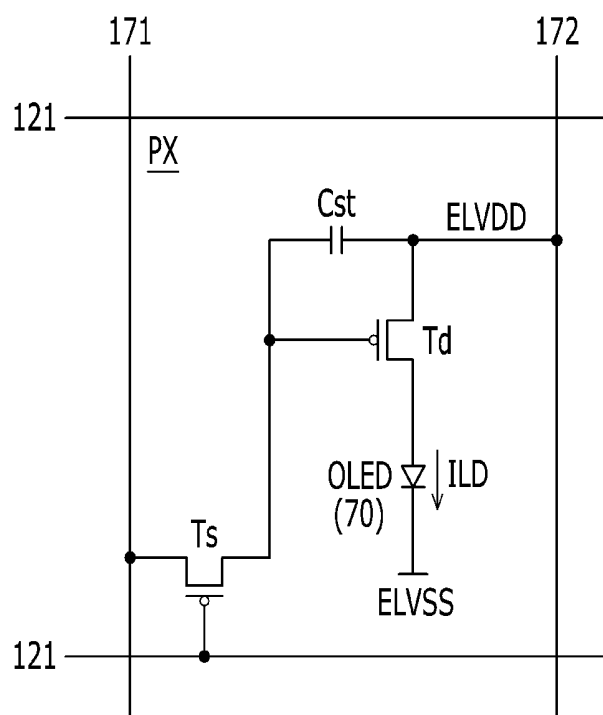


FIG. 4

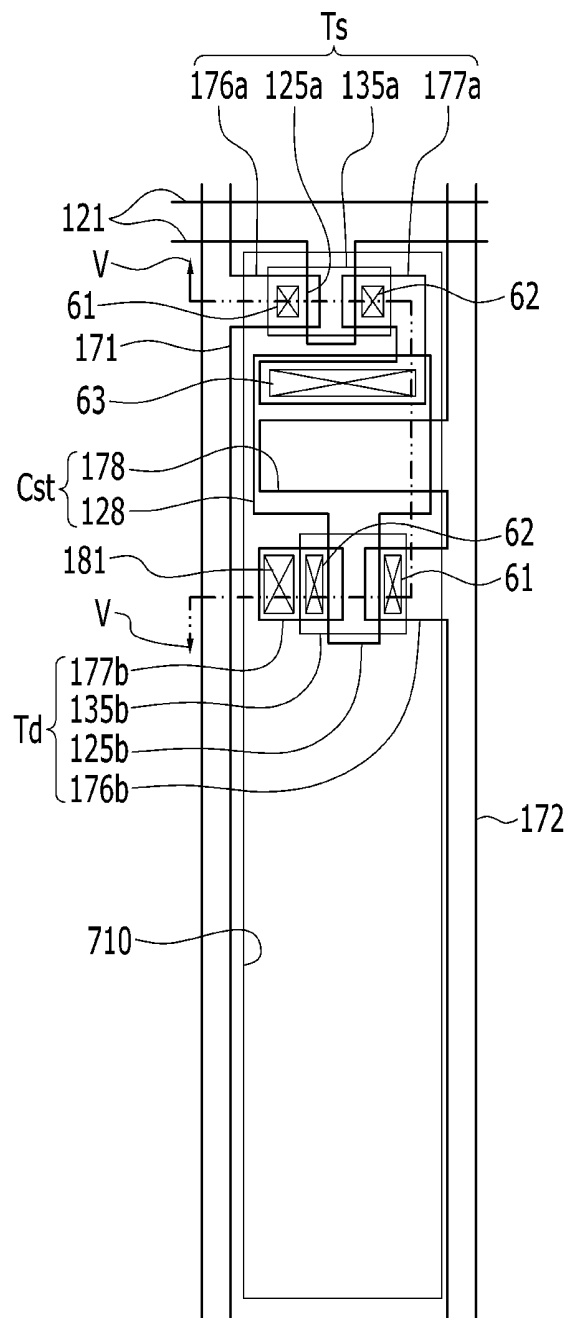
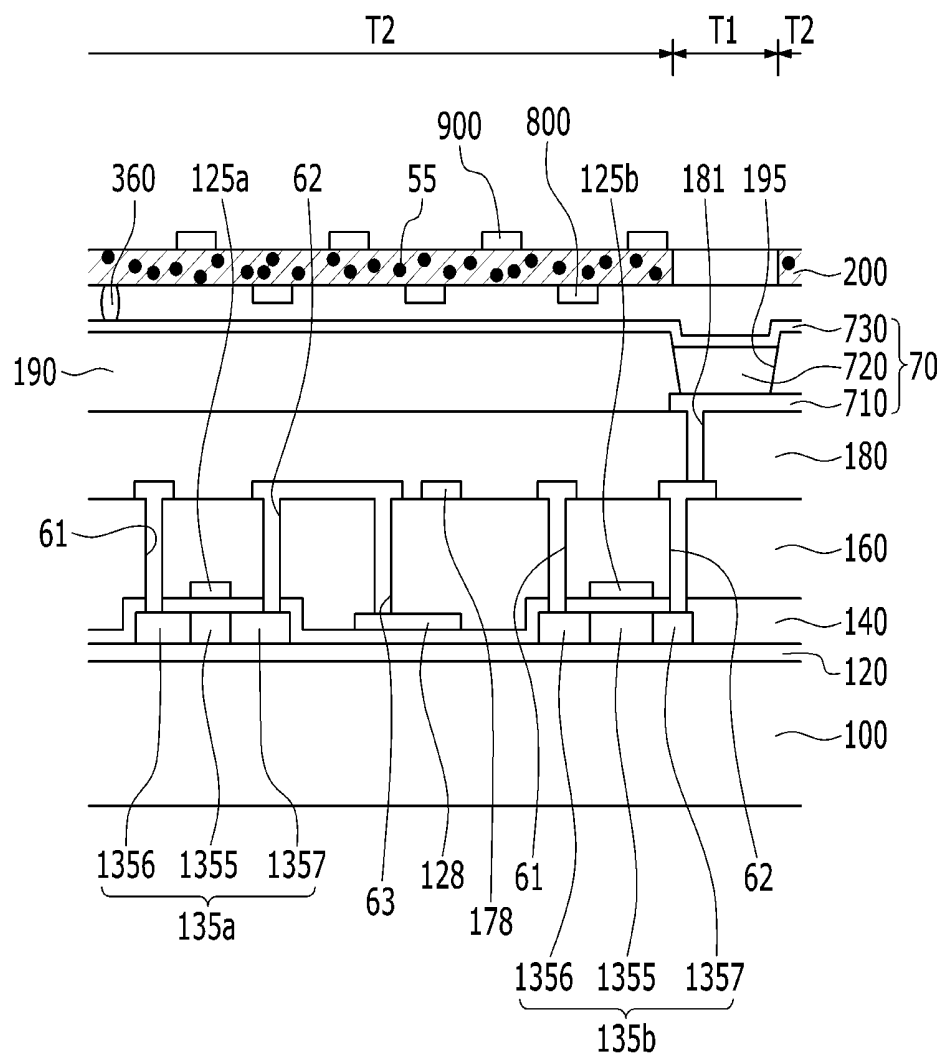


FIG. 5



1

**ORGANIC LIGHT EMITTING DIODE
DISPLAY**

This application claims priority to Korean Patent Application No. 10-2013-0093813 filed on Aug. 7, 2013, and all the benefits accruing therefrom under 35 U.S.C. §119, the entire contents of which are incorporated herein by reference.

BACKGROUND**(a) Field**

The invention relates to an organic light emitting diode (“OLED”) display.

(b) Description of the Related Art

A display device is a device displaying an image, and a display device including an OLED is receiving attention.

Since the OLED display has a self-light emitting characteristic and a separate light source is not employed unlike a liquid crystal display, thickness and weight of the entire display device including the OLED may be reduced to improve a flexible characteristic of the display device. Further, the OLED display has high-quality characteristics such as low power consumption, high luminance and high reaction speed.

The OLED display is portable so as to be capable of being used outside, and is manufactured to have reduced weight and thickness in order to satisfy the aforementioned objectives.

However, when an image is viewed outside, there is a problem in that since sunlight is reflected by a metal reflective layer within the OLED display, contrast and visibility are deteriorated.

SUMMARY

The invention provides an organic light emitting diode (“OLED”) display reducing reflection of external light without increasing a thickness of the OLED display.

An OLED display according to an exemplary embodiment of the invention includes: a substrate; an encapsulation substrate facing the substrate and including a transmission region and an absorption region; a sealant between the substrate and the encapsulation substrate; and a pixel unit between the substrate and the encapsulation substrate, and including a plurality of pixels respectively including an organic light emitting element. The absorption region includes photoreactive crystals.

The photoreactive crystals may include at least one of AgCl, AgBr and AgI.

A size of the photoreactive crystals may be in a range from about 50 angstroms (Å) to about 300 Å.

The transmission region may correspond to a region of an organic emission layer of each organic light emitting element.

The absorption region may enclose the transmission region.

The pixel unit may further include a thin film transistor, a pixel definition layer, and an opening defined in the pixel definition layer. The organic light emitting element may include a first electrode connected to the thin film transistor, an organic emission layer on the first electrode, and a second electrode on the organic emission layer. The opening in the pixel definition layer may expose the first electrode of the organic light emitting element, and the organic emission layer may be within the opening in the pixel definition layer and on the first electrode exposed by the opening.

2

The absorption region may correspond to the pixel definition layer.

The transmission region may correspond to the opening.

The OLED display may further include a touch panel including: a first sensing wire and a second sensing wire respectively disposed at opposing surfaces of the encapsulation substrate, and insulated from and crossing each other.

The OLED display may further include a touch panel including a first sensing wire and a second sensing wire both disposed on a same surface of the encapsulation substrate, and insulated from and crossing each other.

In one or more exemplary embodiment of the invention, when forming the OLED display including the encapsulation substrate having the photoreactive crystals, visibility reduction due to external light may be reduced or effectively prevented without increasing the thickness of the OLED display.

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other features of this disclosure will become more apparent by describing in further detail exemplary embodiments thereof with reference to the accompanying drawings, in which:

FIG. 1 is a schematic cross-sectional view of an exemplary embodiment of an organic light emitting diode (“OLED”) display according to the invention.

FIG. 2 is a schematic top plan view of an exemplary embodiment of an OLED display according to the invention.

FIG. 3 is an equivalent circuit of an exemplary embodiment of one pixel of an OLED display according to the invention.

FIG. 4 is a plan view of an OLED display according to the invention.

FIG. 5 is a cross-sectional view taken along line V-V of FIG. 4.

DETAILED DESCRIPTION

The invention will be described more fully hereinafter with reference to the accompanying drawings, in which exemplary embodiments of the invention are shown. As those skilled in the art would realize, the described exemplary embodiments may be modified in various different ways, all without departing from the spirit or scope of the invention.

The drawings and description are to be regarded as illustrative in nature and not restrictive. Like reference numerals designate like elements throughout the specification.

Furthermore, as the size and thickness of the respective structural components shown in the drawings are arbitrarily illustrated for explanatory convenience, the invention is not necessarily limited to the illustrated sizes and thicknesses.

In the drawings, the thickness of layers, films, panels, regions, etc., are exaggerated for clarity. In the drawings, for better understanding and ease of description, the thicknesses of some layers and areas are exaggerated. It will be understood that when an element such as a layer, film, region, or substrate is referred to as being “on” another element, it can be directly on the other element or intervening elements may also be present.

It will be understood that, although the terms first, second, third, etc., may be used herein to describe various elements, components, regions, layers and/or sections, these elements, components, regions, layers and/or sections should not be limited by these terms. These terms are only used to distinguish one element, component, region, layer or section from another element, component, region, layer or section. Thus, a first element, component, region, layer or section discussed

below could be termed a second element, component, region, layer or section without departing from the teachings of the invention.

Spatially relative terms, such as “lower,” “upper” and the like, may be used herein for ease of description to describe the relationship of one element or feature to another element(s) or feature(s) as illustrated in the figures. It will be understood that the spatially relative terms are intended to encompass different orientations of the device in use or operation, in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as “lower” relative to other elements or features would then be oriented “upper” relative to the other elements or features. Thus, the exemplary term “lower” can encompass both an orientation of above and below. The device may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein interpreted accordingly.

The terminology used herein is for the purpose of describing particular embodiments only and is not intended to be limiting of the invention. As used herein, the singular forms “a,” “an” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will be further understood that the terms “comprises,” “comprising,” “includes” and/or “including,” when used in this specification, specify the presence of stated features, integers, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof.

“About” or “approximately” as used herein is inclusive of the stated value and means within an acceptable range of deviation for the particular value as determined by one of ordinary skill in the art, considering the measurement in question and the error associated with measurement of the particular quantity (i.e., the limitations of the measurement system). For example, “about” can mean within one or more standard deviations, or within $\pm 30\%$, 20% , 10% , 5% of the stated value.

Unless otherwise defined, all terms (including technical and scientific terms) used herein have the same meaning as commonly understood by one of ordinary skill in the art to which this invention belongs. It will be further understood that terms, such as those defined in commonly used dictionaries, should be interpreted as having a meaning that is consistent with their meaning in the context of the relevant art and will not be interpreted in an idealized or overly formal sense unless expressly so defined herein.

All methods described herein can be performed in a suitable order unless otherwise indicated herein or otherwise clearly contradicted by context. The use of any and all examples, or exemplary language (e.g., “such as”), is intended merely to better illustrate the invention and does not pose a limitation on the scope of the invention unless otherwise claimed. No language in the specification should be construed as indicating any non-claimed element as essential to the practice of the invention as used herein.

Hereinafter, the invention will be described in detail with reference to the accompanying drawings.

When an image of an organic light emitting diode (“OLED”) display is viewed outside, there is a problem in that since sunlight is reflected by a metal reflective layer within the OLED display, contrast and visibility are deteriorated.

In order to solve the problem, a circularly polarizing plate is disposed on the OLED display. However, in disposing a polarizing plate on the OLED display, an adhesion layer and a protection layer such as tri-acetyl cellulose (“TAC”) are

included, which increases the thickness and rigidity of the OLED display. Accordingly, there is a limit in increasing flexibility of the OLED display. Further, there is a problem in that a possibility of forming defects caused by foreign particles and the like is increased due to a process because a plurality of layers is laminated. Therefore, there remains a need for an improved OLED display having improved visibility in outdoor environments, and improved flexibility.

In addition, in the accompanying drawings, a “2Tr 1Cap” structured active matrix (“AM”) type OLED display in which a pixel includes two thin film transistors (“TFTs”) and one capacitor is illustrated. However, the invention is not limited thereto. Therefore, an OLED display may have various structures in which a pixel may include a plurality of TFTs and at least one capacitor, a wiring line may be further disposed, and a conventional wiring line may be omitted. Here, a pixel refers to a minimum unit that displays an image, and an OLED display displays an image through a plurality of pixels.

Now, an exemplary embodiment of an OLED display according to the invention will be described in detail with reference to accompanying drawings.

FIG. 1 is a schematic cross-sectional view of an OLED display according to the invention, and FIG. 2 is a schematic top plan view of an OLED display according to the invention.

As shown in FIG. 1, an OLED display includes a substrate **100** and an encapsulation substrate **200** facing each other, and the substrate **100** and the encapsulation substrate **200** are coupled to each other by a sealant **300**.

A pixel unit **400** including a plurality of pixels each including a thin film transistor and an organic light emitting element, and a driver **500** configured to drive the pixel unit **400**, are disposed on the substrate **100**.

The substrate **100** may be, for example, a transparent insulating substrate including glass, quartz, ceramic, or a polymer material, or a metal substrate including stainless steel. The polymer material may include an organic material selected from insulation organic materials, such as polyether sulfone (“PES”), polyacrylate (“PAR”), polyetherimide (“PEI”), polyethylene naphthalate (“PEN”), polyethylene terephthalate (“PET”), polyphenylene sulfide (“PPS”), polyallylate, polyimide, polycarbonate (“PC”), triacetyl cellulose (“TAC”), and cellulose acetate propionate (“CAP”).

The driver **500** includes a driving circuit to drive the pixel unit **400**. The driving circuit may be integrated on the substrate along with the pixel or may be mounted on the substrate **100** as an integrated circuit (“IC”) chip. The driver **500** is electrically connected to the pixel unit **400** by a plurality of signal lines, and each pixel of the pixel unit **400** is controlled by a driving signal transmitted through the plurality of signal lines thereby displaying an image.

Referring to FIG. 2, the encapsulation substrate **200** includes a transmission part transmitting light and an absorption part reflecting light. The encapsulation substrate **200** includes a borosilicate glass including photoreactive crystals **55**. The photoreactive crystals **55** may include at least one of AgCl, AgBr and AgI and are included in the encapsulation substrate **200** in a crystalline state.

The transmission part of the encapsulation substrate **200** is positioned at a display area T1 at which the light is emitted from the pixel unit thereby displaying the image, and the absorption part of the encapsulation substrate **200** is positioned at a non-display area T2 enclosing a region where the light is emitted. The display area T1 may be a region corresponding to an emission layer of an organic light emitting element that is disposed in each pixel of the pixel unit. The photoreactive crystals **55** may be omitted in portions of the encapsulation substrate **200** at the display area T1.

The photoreactive crystals **55** of the absorption part T2 absorb the light while Ag ions are changed into Ag atoms when the light is irradiated, thereby blocking the light. Also, if the light is not irradiated, the Ag atoms are again combined with Cl, Br, or I atoms to form the photoreactive crystals such that the light transmission state is realized, however there is no external light such that the external light is not transmitted.

When only using AgCl as the photoreactive crystals, ultraviolet ("UV") rays near about 190 nanometers (nm) may be absorbed. However, when including AgBr, substantially an entire of visible rays in a visible region may be absorbed.

If a size of the photoreactive crystals is less than about 50 angstroms (Å), the photoreactive crystals react with the light such that there is no light absorption effect. If the size of the photoreactive crystals is over about 300 Å, scattering is generated. In one exemplary embodiment, the size of the photoreactive crystals is in a range of more than about 50 Å and less than about 300 Å.

The size of the crystals is made possible by heat treatment. In an exemplary embodiment, the crystals may be formed by using a laser or by joule heating a metal. When performing the heat treatment by using the joule heating, the joule heat may be formed by using a wire of a touch panel.

The sealant **300** is disposed according to an edge of the substrate **100** and the encapsulation substrate **200** to enclose the pixel unit **400** therebetween, and to form a closed and sealed space along with the substrate **100** and the encapsulation substrate **200**, thereby protecting the pixel unit **400** from an external environment.

Next, the pixel of the OLED display will be described with reference to FIG. 1 and FIG. 2.

FIG. 3 is an equivalent circuit of an exemplary embodiment of one pixel of an OLED display according to the invention.

As shown in FIG. 3, the pixel of the OLED display includes a plurality of signal lines **121**, **171** and **172**, and a plurality of pixels PX connected to the signal lines **121**, **171** and **172** and arranged in a matrix form.

The signal lines include a plurality of scan lines **121** for transmitting scan signals (or gate signals), a plurality of data lines **171** for transmitting data signals, and a plurality of driving voltage lines **172** for transmitting a driving voltage ELVDD. The scan lines **121** run parallel with each other in a row direction, and the data lines **171** and the driving voltage lines **172** run parallel with each other in a column direction. Each of the pixels PX includes a switching thin film transistor Ts, a driving thin film transistor Td, a storage capacitor Cst and an OLED **70**.

The switching thin film transistor Ts has a control terminal, an input terminal and an output terminal. The control terminal is connected to the scan line **121**, the input terminal is connected to the data line **171** and the output terminal is connected to the driving thin film transistor Td. The switching thin film transistor Ts transmits a data signal applied to the data line **171** to the driving thin film transistor Td in response to a scan signal applied to the scan lines **121**.

The driving thin film transistor Td also has a control terminal, an input terminal and an output terminal. The control terminal is connected to the switching thin film transistor Ts, the input terminal is connected to the driving voltage line **172**, and the output terminal is connected to the OLED. The driving thin film transistor Td causes an output current ILD to flow, which varies in amplitude in accordance with a voltage applied between the control terminal and the output terminal.

The storage capacitor Cst is connected between the control terminal and input terminal of the driving thin film transistor Td. The storage capacitor Cst charges a data signal applied to

the control terminal of the driving thin film transistor Td, and maintains the data signal after the switching thin film transistor Ts is turned off.

The OLED **70** has an anode connected to the output terminal of the driving thin film transistor Td and a cathode connected to a common voltage ELVSS. The OLED **70** displays an image by emitting light with different intensities according to an output current ILD of the driving thin film transistor Td.

Next, a detailed structure of the pixel of the OLED display shown in FIG. 3 will be described with reference to FIG. 4 and FIG. 5.

FIG. 4 is a plan view of an exemplary embodiment of an OLED display according to the invention, and FIG. 5 is a cross-sectional view taken along line V-V of FIG. 4.

As shown in FIG. 4 and FIG. 5, a buffer layer **120** is disposed on a substrate **100** of an OLED display.

The buffer layer **120** may have a single-layer structure of silicon nitride (SiNx), or a dual-layer structure of silicon nitride (SiNx) and silicon oxide (SiO₂) laminated to each other.

The buffer layer **120** prevents penetration of unnecessary elements, such as impurities or moisture to components of the OLED display, and helps planarize the surface.

A switching semiconductor **135a** and a driving semiconductor **135b** are disposed on the buffer layer **120**, and are spaced apart from each other.

These semiconductors **135a** and **135b** may include a polysilicon or oxide semiconductor.

The oxide semiconductor may include one selected from oxides based on titanium (Ti), hafnium (Hf), zirconium (Zr), aluminum (Al), tantalum (Ta), germanium (Ge), zinc (Zn), gallium (Ga), tin (Sn), or indium (In), and complex oxides thereof, such as zinc oxide (ZnO), indium-gallium-zinc oxide (InGaZnO₄), indium-zinc oxide (Zn—In—O), zinc-tin oxide (Zn—Sn—O), indium-gallium oxide (In—Ga—O), indium-tin oxide (In—Sn—O), indium-zirconium oxide (In—Zr—O), indium-zirconium-zinc oxide (In—Zr—Zn—O), indium-zirconium-tin oxide (In—Zr—Sn—O), indium-zirconium-gallium oxide (In—Zr—Ga—O), indium-aluminum oxide (In—Al—O), indium-zinc-aluminum oxide (In—Zn—Al—O), indium-tin-aluminum oxide (In—Sn—Al—O), indium-aluminum-gallium oxide (In—Al—Ga—O), indium-tantalum oxide (In—Ta—O), indium-tantalum-zinc oxide (In—Ta—Zn—O), indium-tantalum-tin oxide (In—Ta—Sn—O), indium-tantalum-gallium oxide (In—Ta—Ga—O), indium-germanium oxide (In—Ge—O), indium-germanium-zinc oxide (In—Ge—Zn—O), indium-germanium-tin oxide (In—Ge—Sn—O), indium-germanium-gallium oxide (In—Ge—Ga—O), titanium-indium-zinc oxide (Ti—In—Zn—O), and hafnium-indium-zinc oxide (Hf—In—Zn—O). If the semiconductors **135a** and **135b** include the oxide semiconductor, a separate protective layer (not shown) may be added to protect the oxide semiconductor from the outside environment such as from a high temperature.

The switching semiconductor **135a** and the driving semiconductor **135b** are respectively divided into a channel region **1355**, and a source region **1356** and drain region **1357** respectively disposed at sides of the channel region **1355**. The impurities in the semiconductors vary according to the type of thin film transistor including the semiconductors, and may be N-type impurities or P-type impurities.

The channel regions **1355** of the switching semiconductor **135a** and the driving semiconductor **135b** may include polysilicon not doped with impurities, that is, an intrinsic semiconductor, and the source regions **1356** and drain regions **1357** of the switching semiconductor **135a** and the driving

semiconductor **135b** may include polysilicon doped with conductive impurities, that is, an impurity semiconductor.

A gate insulating film **140** is disposed on the switching semiconductor **135a** and the driving semiconductor **135b**.

The gate insulating film **140** may be a single layer, or a plurality of layers including at least one of silicon nitride and silicon oxide.

A scan line **121**, a driving gate electrode **125b**, and a first storage capacitor plate **128** are disposed on the gate insulating film **140**.

The gate line **121** may be the first signal line of FIG. 3, and extends in a transverse (e.g., row or horizontal) direction to transmit a scan signal. The gate line **121** includes a switching gate electrode **125a** protruded from a main portion thereof toward the switching semiconductor **135a**. The driving gate electrode **125b** protrudes from the first storage capacitor plate **128** toward the driving semiconductor layer **135b**. The switching gate electrode **125a** and the driving gate electrode **125b** overlap the channel regions **1355**, respectively.

An interlayer insulating film **160** is disposed on the scan line **121**, the driving gate electrode **125b** and the first storage capacitor plate **128**.

Like the gate insulating film **140**, the interlayer insulating film **160** may include silicon nitride or silicon oxide.

Source contact holes **61** and drain contact holes **62** are defined in the interlayer insulating film **160** and the gate insulating film **140** to expose the source regions **1356** and the drain regions **1357**, and storage contact holes **63** are defined therein to expose part of the first storage capacitor plate **128**.

A data line **171** including a switching source electrode **176a**, a driving voltage line **172** including a driving source electrode **176b** and a second storage capacitor plate **178**, and a switching drain electrode **177a** and a driving drain electrode **177b** that are connected to the first storage capacitor plate **128** are disposed on the interlayer insulating film **160**. The data line **171** may be the second signal line of FIG. 3, and the driving voltage line **172** may be the third signal line.

The data line **171** transfers a data signal, and extends in a direction crossing the gate line **121**. The driving voltage line **172** transfers a driving voltage, and is separated from the data line **171** and extends in the same direction as the data line **171**.

The switching source electrode **176a** protrudes from a main portion of the data line **171** toward the switching semiconductor layer **135a**, and the driving source electrode **176b** protrudes from a main portion of the driving voltage line **172** toward the driving semiconductor layer **135b**. The switching source electrode **176a** and the driving source electrode **176b** are respectively connected to the source regions **1356** through the source contact holes **61**. The switching drain electrode **177a** faces the switching source electrode **176a** with respect to the switching gate electrode **125a**, the driving drain electrode **177b** faces the driving source electrode **176b** with respect to the driving gate electrode **125b**, and the switching drain electrode **177a** and the driving drain electrode **177b** are respectively connected to the drain regions **1357** through the drain contact holes **62**.

The switching drain electrode **177a** is extended and electrically connected to the first storage capacitor plate **128** and the driving gate electrode **125b** through the storage contact holes **63** defined in the interlayer insulating layer **160**.

The second storage capacitor plate **178** protrudes from the main portion of the driving voltage line **172**, and overlaps the first storage capacitor plate **128**. Accordingly, the first storage capacitor plate **128** and the second storage capacitor plate **178** form the storage capacitor **Cst** by using the interlayer insulating film **160** as a dielectric material therebetween.

The switching semiconductor layer **135a**, the switching gate electrode **125a**, the switching source electrode **176a** and the switching drain electrode **177a** form the switching thin film transistor **Ts**, and the driving semiconductor layer **135b**, the driving gate electrode **125b**, the driving source electrode **176b** and the driving drain electrode **177b** form the driving thin film transistor **Td**.

A protective film **180** is disposed on the switching source electrode **176a**, the driving source electrode **176b**, the switching drain electrode **177a** and the driving drain electrode **177b**.

A first electrode **710** is disposed on the protective layer **180**.

The first electrode **710** is electrically connected to the driving drain electrode **177b** of the driving thin film transistor **Td** through a contact hole **181** defined in the interlayer insulating layer **160**, thereby being the anode of the OLED **70**.

The first electrode **710** may include a transparent conducting material such as indium tin oxide ("ITO"), indium zinc oxide ("IZO"), zinc oxide (ZnO), or indium oxide (In₂O₃), or a reflective metal such as lithium (Li), calcium (Ca), lithium fluoride/calcium (LiF/Ca), lithium fluoride/aluminum (LiF/Al), aluminum (Al), silver (Ag), magnesium (Mg) or gold (Au), but not being limited thereto.

A pixel definition layer **190** is disposed on edge portions of the first electrode **710** and the protective film **180**. An opening **195** is defined in the pixel definition layer **190** exposing the first electrode **710**.

The pixel definition layer **190** may include a resin such as polyacrylate resin or polyimide resin, a silica-based inorganic material, or the like.

An organic emission layer **720** is disposed in the opening **195** of the pixel defining layer **190**. The organic emission layer **720** includes an emission layer and a plurality of layers including one or more of a hole-injection layer ("HIL"), a hole-transporting layer ("HTL"), an electron-transporting layer ("ETL") and an electron-injection layer ("EIL"). If the organic emission layer **720** includes all of the aforementioned layers, the HIL may be positioned on the first electrode **710** serving as an anode, and the HTL, the emission layer, the ETL and the EIL may be sequentially laminated on the first electrode **710**.

The organic emission layer **720** may include a red organic emission layer for emitting red light, a green organic emission layer for emitting green light and a blue organic emission layer for emitting blue light. The red organic emission layer, the green organic emission layer, and the blue organic emission layer are respectively disposed in red, green, and blue pixels of the OLED display, thereby displaying a color image.

In one exemplary embodiment, the red organic emission layer, green organic emission layer and blue organic emission layer of the organic emission layer **720** may be respectively laminated on the red pixel, green pixel and blue pixel, and a red color filter, a green color filter and a blue color filter may be disposed for the respective pixels, thereby displaying a color image. In another exemplary embodiment, a white organic emission layer for emitting white light may be collectively disposed on all of the red, green and blue pixels, and a red color filter, a green color filter and a blue color filter may be disposed for the respective pixels, thereby displaying a color image. If the white organic emission layer and the color filters are used to display a color image, a deposition mask for depositing the red, green and blue organic emission layers on the respective pixels, e.g., the red, green and blue pixels may be omitted, in a method of manufacturing the OLED display.

The white organic emission layer described in the exemplary embodiment may be formed as one organic emission layer or a plurality of organic emission layers that are lami-

nated to emit white light. In one exemplary embodiment, for example, as the plurality of organic emission layers, at least one yellow organic emission layer and at least one blue organic emission layer may be combined to emit white light, at least one cyan organic emission layer and at least one red organic emission layer may be combined to emit white light, or at least one magenta organic emission layer and at least one green organic emission layer may be combined to emit white light.

A second electrode **730** is disposed on the pixel definition layer **190** and the organic emission layer **720**. The second electrode **730** may include a transparent conducting material such as ITO, IZO, ZnO or In₂O₃, or a reflective metal such as lithium (Li), calcium (Ca), lithium fluoride/calcium (LiF/Ca), lithium fluoride/aluminum (LiF/Al), aluminum (Al), silver (Ag), magnesium (Mg), or gold (Au). The second electrode **730** becomes the cathode of the OLED **70**. The first electrode **710**, the organic emission layer **720** and the second electrode **730** collectively form the OLED **70**, which may otherwise be referred to as an organic light emitting element of the OLED display.

A spacer **360** is disposed on the second electrode **730**. The spacer **360** maintains a predetermined interval between the substrate **100** and the encapsulation substrate **200**.

The encapsulation substrate **200** is positioned on the spacer **360** and the OLED **70** is sealed between the substrate **100**, the encapsulation substrate **200** and the spacer **360**.

As shown in FIG. 1 and FIG. 2, the encapsulation substrate **200** includes the transmission part and the absorption part, and the absorption part includes the photoreactive crystals. The absorption part is positioned at the non-display area T2 such as including the pixel definition layer **190**, and the transmission part is positioned at the display area T1 such as including the opening **195** defined in the pixel definition layer **190**.

A plurality of first sensing wires (Tx) **800** and second sensing wires (Rx) **900** are disposed on one surface or both of opposing surfaces of the encapsulation substrate **200**.

For better understanding and ease of description, one surface of the encapsulation substrate **200** sealed by the sealant **300** is referred to as a lower surface and the opposing other surface that is not sealed and is exposed outside is referred to as an upper surface.

The first sensing wires (Tx) **800** and the second sensing wires (Rx) **900** are insulated from each other, and in a plan view, the first sensing wires (Tx) **800** and the second sensing wires (Rx) are each elongated and cross each other thereby forming a touch panel for touch sensing. In the touch panel including the first sensing wires (Tx) **800** and the second sensing wires (Rx) as a capacitive type of touch panel, if a touch voltage is applied to the second sensing wire (Rx) **900** and the first sensing wire (Tx) **800** that are crossed with each other and any one position along the encapsulation substrate is applied with a touch implemented through a input means such as a finger or a pen, a voltage drop is generated thereby determining position coordinates of the touch.

For the first sensing wires (Tx) **800** and the second sensing wires (Rx), with respect to the encapsulation substrate **200**, the second sensing wires (Rx) **900** are disposed on the upper surface of the encapsulation substrate **200** and the first sensing wires (Tx) **800** are disposed on the lower surface of the encapsulation substrate **200**. Also, although not shown, the first sensing wires (Tx) **800** and the second sensing wires (Rx) may both be disposed on the upper surface of the encapsulation substrate **200**, via an insulating layer therebetween.

As described above, if an additional substrate is omitted in the OLED display and the first sensing wires (Tx) **800** and the second sensing wires (Rx) are disposed on one surface or both surfaces of the single encapsulation substrate **200**, the manu-

facturing process of the OLED display may be simplified and an overall thickness thereof may be thin.

What is claimed is:

1. An organic light emitting diode display comprising:
a substrate;

an encapsulation substrate facing the substrate, and comprising a transmission region through which light is transmitted and an absorption region through which the light is not transmitted;

a sealant between the substrate and the encapsulation substrate; and

a pixel unit between the substrate and the encapsulation substrate, and comprising a plurality of pixels respectively comprising an organic light emitting element, wherein the absorption region of the encapsulation substrate comprises photoreactive crystals.

2. The organic light emitting diode display of claim 1, wherein

the photoreactive crystals comprise at least one of AgCl, AgBr and AgI.

3. The organic light emitting diode display of claim 2, wherein

a size of the photoreactive crystals is in a range from about 50 angstroms to about 300 angstroms.

4. The organic light emitting diode display of claim 1, wherein

the transmission region of the encapsulation substrate corresponds to a region of an organic emission layer of each organic light emitting element of the pixel unit.

5. The organic light emitting diode display of claim 4, wherein

the absorption region of the encapsulation substrate encloses the transmission region.

6. The organic light emitting diode display of claim 1, wherein

the pixel unit further comprises:

a thin film transistor; and

a pixel definition layer, and an opening defined in the pixel definition layer; and

the organic light emitting element comprises:

a first electrode connected to the thin film transistor;

an organic emission layer disposed on the first electrode; and

a second electrode disposed on the organic emission layer,

wherein

the opening in the pixel definition layer exposes the first electrode of the organic light emitting element, and the organic emission layer is within the opening in the pixel definition layer and on the first electrode exposed by the opening.

7. The organic light emitting diode display of claim 6, wherein

the absorption region of the encapsulation substrate corresponds to the pixel definition layer of the pixel unit.

8. The organic light emitting diode display of claim 6, wherein

the transmission region of the encapsulation substrate corresponds to the opening defined in the pixel definition layer of the pixel unit.

9. The organic light emitting diode display of claim 1, further comprising a touch panel comprising:

a first sensing wire and a second sensing wire respectively disposed at opposing surfaces of the encapsulation substrate, and insulated from and crossing each other.

10. The organic light emitting diode display of claim 1, further comprising a touch panel comprising:

a first sensing wire and a second sensing wire both disposed on a same surface of the encapsulation substrate, and insulated from and crossing each other.

11. A method of manufacturing an organic light emitting diode display, comprising:
- providing a substrate and an encapsulation substrate facing each other;
 - providing a pixel unit comprising a plurality of pixels 5
respectively comprising an organic light emitting element, between the substrate and the encapsulation substrate; and
 - coupling the substrate and the encapsulation substrate to each other by a sealant, to seal the pixel unit therebetween; 10
- wherein
- the encapsulation substrate comprises a transmission region through which light is transmitted and an absorption region through which the light is not transmitted 15
and;
 - the absorption region of the encapsulation substrate comprises photoreactive crystals.
12. The method of claim 11, wherein
- the photoreactive crystals include at least one of AgCl, AgBr and AgI. 20
13. The method of claim 12, wherein
- a size of the photoreactive crystals is in a range from about 50 angstroms to about 300 angstroms.
14. The method of claim 11, wherein
- the transmission region of the encapsulation substrate corresponds to a region of an organic emission layer of each 25
organic light emitting element of the pixel unit.

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专利名称(译)	有机发光二极管显示器		
公开(公告)号	US9048205	公开(公告)日	2015-06-02
申请号	US14/285920	申请日	2014-05-23
[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	HAN BYUNG UK		
发明人	HAN, BYUNG-UK		
IPC分类号	H01L27/32 H01L51/56		
CPC分类号	H01L27/3232 H01L51/56 H01L27/323 H01L51/52 H01L51/5237 H01L2251/53 H01L27/3244 H01L51/525 H01L51/5284 H01L2251/558 H05B33/04		
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优先权	1020130093813 2013-08-07 KR		
其他公开文献	US20150041774A1		
外部链接	Espacenet USPTO		

摘要(译)

有机发光二极管包括：基板；封装基板，面向基板并包括透射光的透射区域和不透光的吸收区域；基板和封装基板之间的密封剂；基板和封装基板之间的像素单元，包括分别包括有机发光元件的多个像素。封装基板的吸收区域包括光反应晶体。

